



May 22, 1998

GAU 2753
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To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

1-27
29-31
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Subject:

Serial No. 09/046,007 03/23/98

C.C. Han, M.M. Chen, C.T. Horng,
Terry Torng

A NOVEL SINGLE STRIPE
MAGNETORESISTIVE (MR) HEAD

Grp. Art Unit: 2753

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INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

Each of these following Patents and/or Publications have
been mentioned and described in the Specification
of the Subject Patent Application:

U.S. Patent 5,508,866 to Gill et al, "Magnetoresistive Sensor Having Exchange-Coupled Stabilization For Transverse Bias Layer", discloses a soft adjacent layer (SAL) magnetoresistive (MR) sensor element comprising an exchange coupled antiferromagnetic bias layer contacting a SAL within the SAL MR sensor element.

U.S. Patent 5,483,402 to Batra, "Magneto Resistive Head Having Symmetric Off-Track Performance Profile", discloses a soft adjacent layer (SAL) magnetoresistive (MR) sensor element having electrical leads whose planar surfaces are canted with respect to the easy axis of magnetization of the MR layer.

U.S. Patent 5,573,809 to Nix et al, "Process For Forming A Magnetoresistive Device", discloses a soft adjacent layer (SAL) magnetoresistive (MR) sensor element comprising a MR layer having a permanent magnet layer formed at etch of its ends, where the MR layer and permanent magnet layers are separated by a tantalum or titanium spacer layer from a SAL within the SAL magnetoresistive sensor element.

U.S. Patent 5,715,120 to Gill, "Magnetoresistive Sensor With Enhanced Magnetoresistive Effect", discloses a soft adjacent layer (SAL) magnetoresistive (MR) sensor element employing a dielectric spacer layer separating a soft adjacent layer from a magnetoresistive layer within the soft adjacent layer magnetoresistive element, where the SAL is further biased with an antiferromagnetic material layer contacting a surface of the SAL opposite the dielectric layer.

Sincerely,



Stephen B. Ackerman,
Reg. No. 37761